# V30M120CxM3, VI30M120CxM3

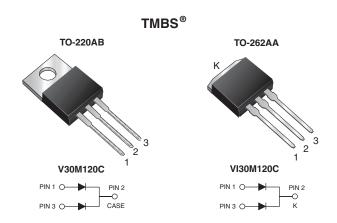
Vishay General Semiconductor

HALOGEN

FREE

# **Dual High-Voltage Trench MOS Barrier Schottky Rectifier**

Ultra Low  $V_F = 0.52 \text{ V}$  at  $I_F = 5 \text{ A}$ 



PRIMARY CHARACTERISTICS					
I <sub>F(AV)</sub>	2 x 15 A				
$V_{RRM}$	120 V				
I <sub>FSM</sub>	150 A				
V <sub>F</sub> at I <sub>F</sub> = 15 A	0.68 V				
T <sub>J</sub> max.	175 °C				
Package	TO-220AB, TO-262AA				
Diode variations	Dual common cathode				

## **FEATURES**

- Trench MOS Schottky technology
- · Low forward voltage drop, low power losses

High efficiency operation

• Solder dip 275 °C max. 10 s, per JESD 22-B106

Solder dip 275 °C max. To s, per JESD 22-B Too

• AEC-Q101 qualified

 Material categorization: For definitions of compliance please see <a href="https://www.vishay.com/doc?99912"><u>www.vishay.com/doc?99912</u></a>

## TYPICAL APPLICATIONS

For use in high frequency DC/DC converters, switching power supplies, freewheeling diodes, OR-ing diode, and reverse battery protection.

## **MECHANICAL DATA**

Case: TO-220AB and TO-262AA

Molding compound meets UL 94 V-0 flammability rating Base P/N-M3 - halogen-free, RoHS-compliant, and

commercial grade

Base P/NHM3 - halogen-free, RoHS-compliant, and

AEC-Q101 qualified

Terminals: Matte tin plated leads, solderable per

J-STD-002 and JESD 22-B102

M3 suffix meets JESD 201 class 1A whisker test, HM3 suffix

meets JESD 201 class 2 whisker test

Polarity: As marked

Mounting Torque: 10 in-lbs maximum

MAXIMUM RATINGS (T <sub>A</sub> = 25 °C unless otherwise noted)						
PARAMETER		SYMBOL	V30M120C	VI30M120C	UNIT	
Maximum repetitive peak reverse voltage		$V_{RRM}$	120		V	
Maximum average forward rectified current (fig. 1)	per device	I <sub>F(AV)</sub>	30		A	
	per diode		15			
Peak forward surge current 8.3 ms single half sine-wave superimposed on rated load per diode		I <sub>FSM</sub>	150		1	
Voltage rate of change (rated V <sub>R</sub> )		dV/dt	10 000		V/µs	
Operating junction and storage temperature range		T <sub>J</sub> , T <sub>STG</sub>	-40 to	+175	°C	



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<b>ELECTRICAL CHARACTERISTICS</b> (T <sub>A</sub> = 25 °C unless otherwise noted)							
PARAMETER	TEST CONDITIONS		SYMBOL	TYP.	MAX.	UNIT	
Instantaneous forward voltage per diode	$I_F = 5 A$	T <sub>A</sub> = 25 °C	V <sub>F</sub> <sup>(1)</sup>	0.60	-	V	
	I <sub>F</sub> = 7.5 A			0.67	-		
	I <sub>F</sub> = 15 A			0.87	0.98		
	$I_F = 5 A$	T <sub>A</sub> = 125 °C		0.52	-		
	I <sub>F</sub> = 7.5 A			0.57	-		
	I <sub>F</sub> = 15 A			0.68	0.76		
Reverse current per diode	V <sub>R</sub> = 90 V	T <sub>A</sub> = 25 °C	I <sub>R</sub> (2)	3.5	-	μΑ	
		T <sub>A</sub> = 125 °C		2	-	mA	
	I Vp = 120 V ⊢	T <sub>A</sub> = 25 °C		-	800	μA	
		T <sub>A</sub> = 125 °C		5	27	mA	

### **Notes**

(1) Pulse test: 300 µs pulse width, 1 % duty cycle

(2) Pulse test: Pulse width ≤ 5 ms

THERMAL CHARACTERISTICS (T <sub>A</sub> = 25 °C unless otherwise noted)					
PARAMETER		SYMBOL	V30M120C	VI30M120C	UNIT
	per diode	В	2.2		°C/W
Typical thermal resistance (1)	per device	− R <sub>θJC</sub>	1.3		
	per device	R <sub>0JA</sub> (2)	45	55	

#### Notes

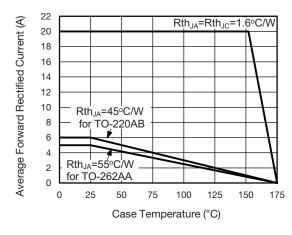
<sup>(1)</sup> The heat generated must be less than the thermal conductivity from junction-to-ambient  $dP_D/dT_J < 1/R_{\theta,JA}$ 

<sup>(2)</sup> Free air, without heatsink

ORDERING INFORMATION (Example)							
PACKAGE	PREFERRED P/N	UNIT WEIGHT (g)	PACKAGE CODE	BASE QUANTITY	DELIVERY MODE		
TO-220AB	V30M120C-M3/4W	1.89	4W	50/tube	Tube		
TO-220AB	V30M120CHM3/4W	1.89	4W	50/tube	Tube		
TO-262AA	VI30M120C-M3/4W	1.45	4W	50/tube	Tube		
TO-262AA	VI30M120CHM3/4W	1.45	4W	50/tube	Tube		

## Note

## RATINGS AND CHARACTERISTICS CURVES (T<sub>A</sub> = 25 °C unless otherwise noted)





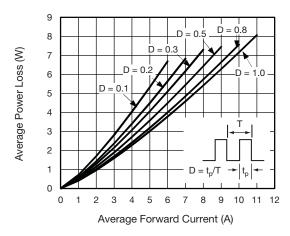


Fig. 2 - Forward Power Loss Characteristics Per Diode

<sup>(1)</sup> AEC-Q101 qualified





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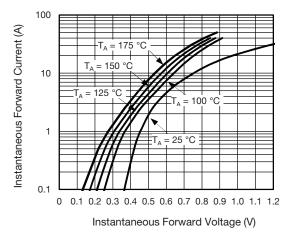


Fig. 3 - Typical Instantaneous Forward Characteristics Per Diode

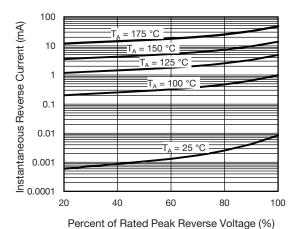


Fig. 4 - Typical Reverse Characteristics Per Diode

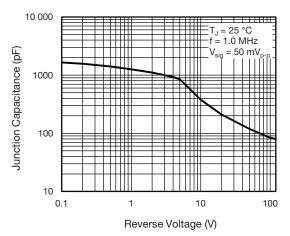


Fig. 5 - Typical Junction Capacitance Per Diode

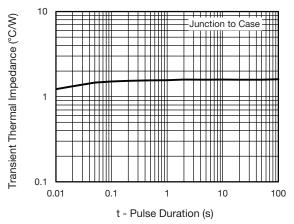
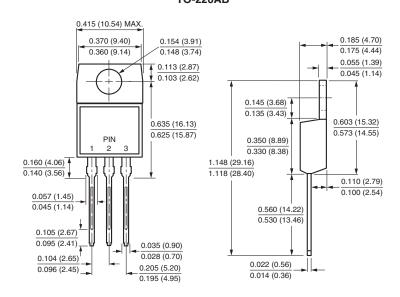


Fig. 6 - Typical Transient Thermal Impedance Per Diode

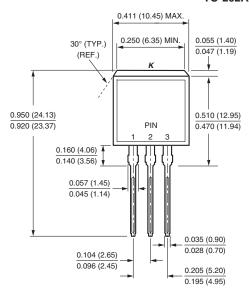


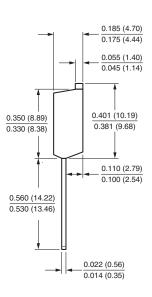
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# PACKAGE OUTLINE DIMENSIONS in inches (millimeters) TO-220AB



### TO-262AA







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